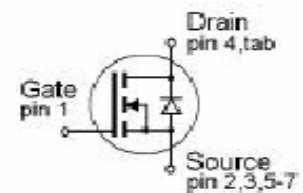


**OptiMOS<sup>®</sup> - T Power-Transistor**
**Features**

- N-channel Logic Level - Enhancement mode
- Automotive AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green package (lead free)
- Ultra low Rds(on)
- 100% Avalanche tested

**Product Summary**

$V_{DS}$	40	V
$R_{DS(on),max}$	2.7	mΩ
$I_D$	160	A

**PG-TO263-7-3**


Type	Package	Ordering Code	Marking
IPB160N04S2L-03	PG-TO263-7-3	SP0002-18153	P2N04L03

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}$	160	A
		$T_C=100\text{ °C}^{2)}$	160	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	640	
Avalanche energy, single pulse	$E_{AS}$	$I_D=80\text{ A}, R_{GS}=25\text{ Ω}$	810	mJ
	$V_{GS}$		±20	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	300	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Thermal characteristics<sup>2)</sup></b>						
Thermal resistance, junction - case	$R_{thJC}$		-	-	0.5	K/W
SMD version, device on PCB	$R_{thJA}$	minimal footprint	-	-	62	
		6 cm <sup>2</sup> cooling area <sup>3)</sup>	-	-	40	

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**

**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$	1.2	1.6	2	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=40\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	$\mu\text{A}$
		$V_{DS}=40\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}^{2)}$	-	10	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5\text{ V}, I_D=80\text{ A},$ SMD version	-	2.8	3.7	m $\Omega$
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=80\text{ A},$ SMD version	-	2.0	2.7	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics<sup>2)</sup>**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V},$ $f=1\text{ MHz}$	-	6000	-	pF
Output capacitance	$C_{oss}$		-	2200	-	
Reverse transfer capacitance	$C_{rss}$		-	700	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=20\text{ V}, V_{GS}=10\text{ V},$ $I_D=160\text{ A}, R_G=1.1\ \Omega$	-	20	-	ns
Rise time	$t_r$		-	51	-	
Turn-off delay time	$t_{d(off)}$		-	75	-	
Fall time	$t_f$		-	30	-	

**Gate Charge Characteristics<sup>2)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=32\text{ V}, I_D=160\text{ A},$ $V_{GS}=0\text{ to }5\text{ V}$	-	20	28	nC
Gate to drain charge	$Q_{gd}$		-	46	90	
Gate charge total	$Q_g$		-	163	230	
Gate plateau voltage	$V_{plateau}$		-	3.4	-	V

**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	160	A
Diode pulse current	$I_{S,pulse}$		-	-	640	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=80\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.84	1.3	V

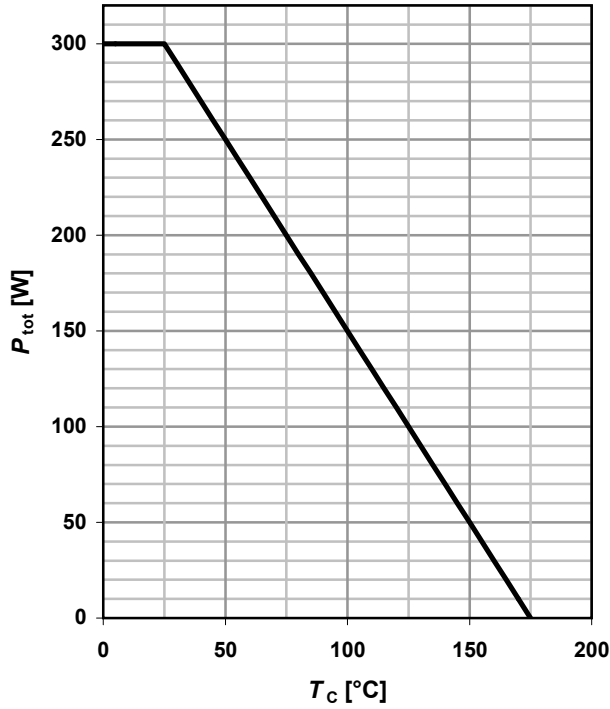
<sup>1)</sup> Current is limited by bondwire; with an  $R_{thJC} = 0.5\text{K/W}$  the chip is able to carry 243A at 25°C. For detailed information see Application Note ANPS071E at [www.infineon.com/optimos](http://www.infineon.com/optimos)

<sup>2)</sup> Defined by design. Not subject to production test.

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

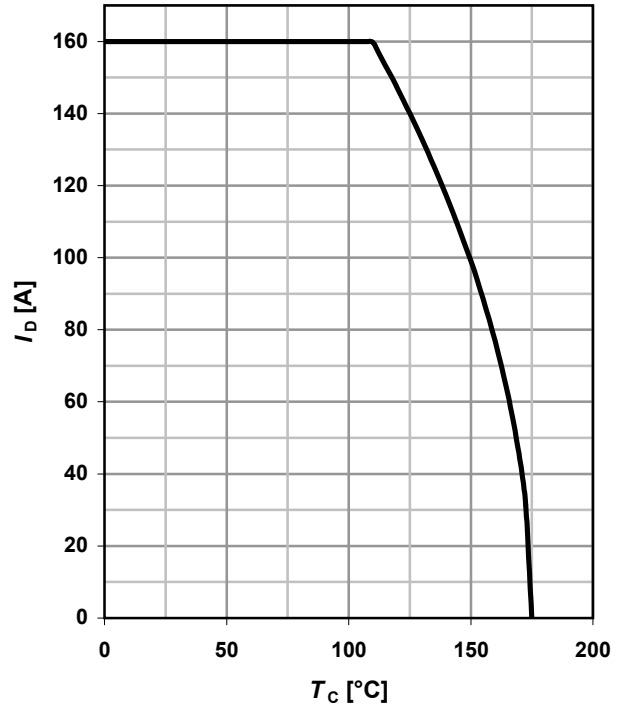
**1 Power dissipation**

$P_{tot}=f(T_C)$



**2 Drain current**

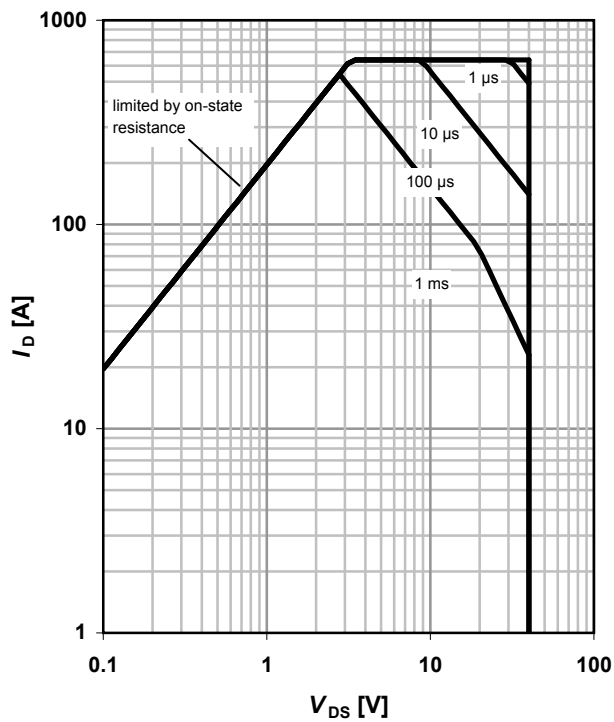
$I_D=f(T_C); V_{GS} \geq 10\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

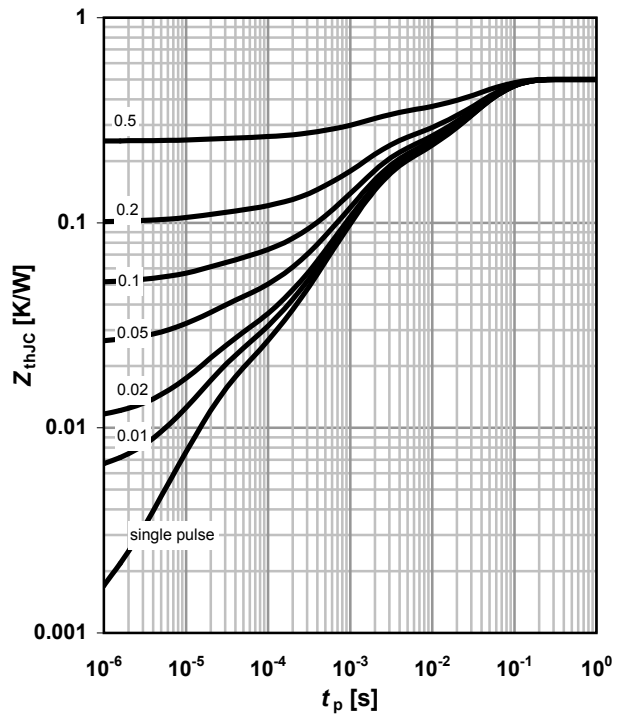
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

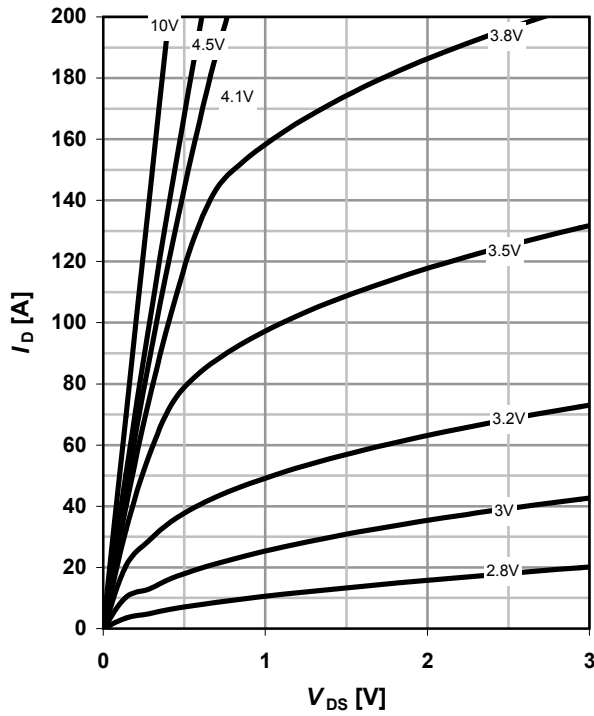
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

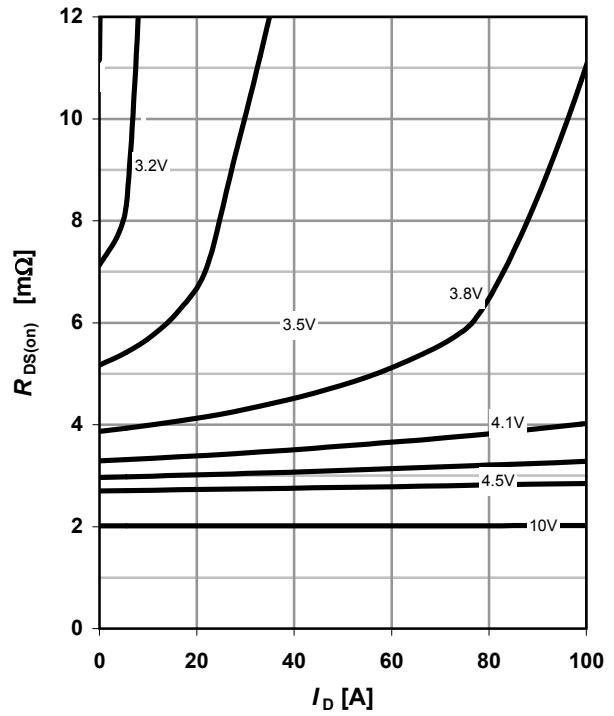
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

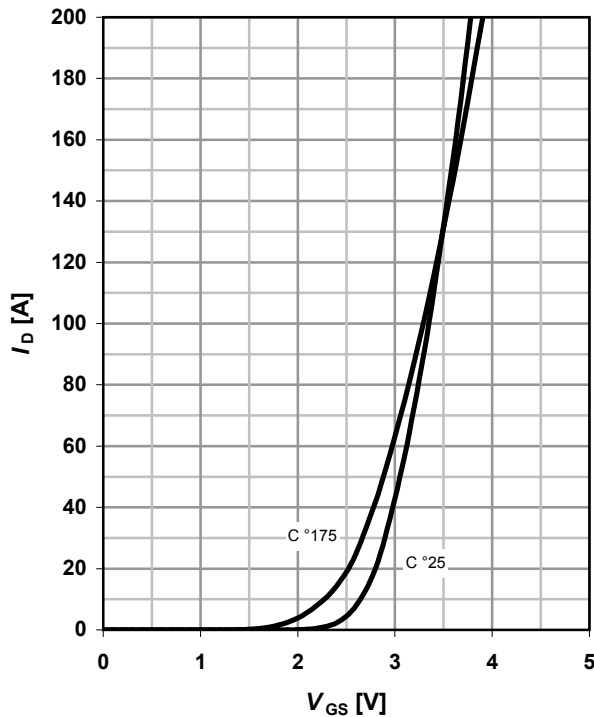
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

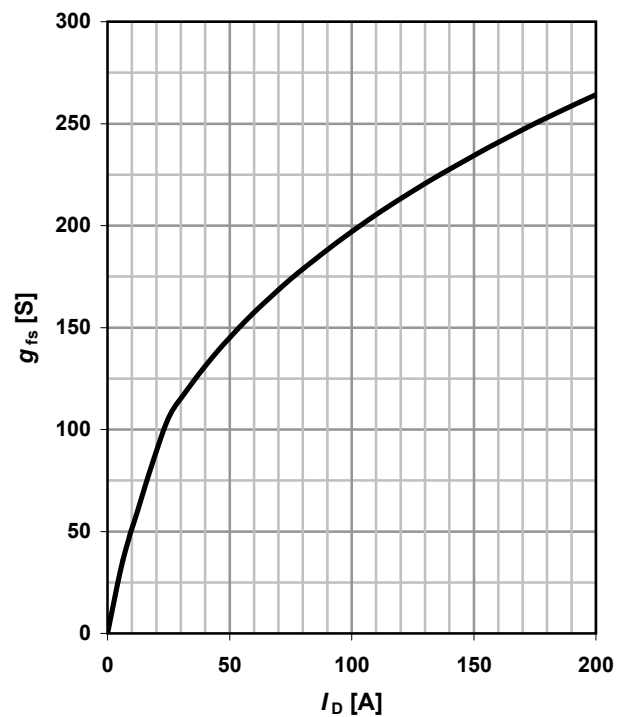
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



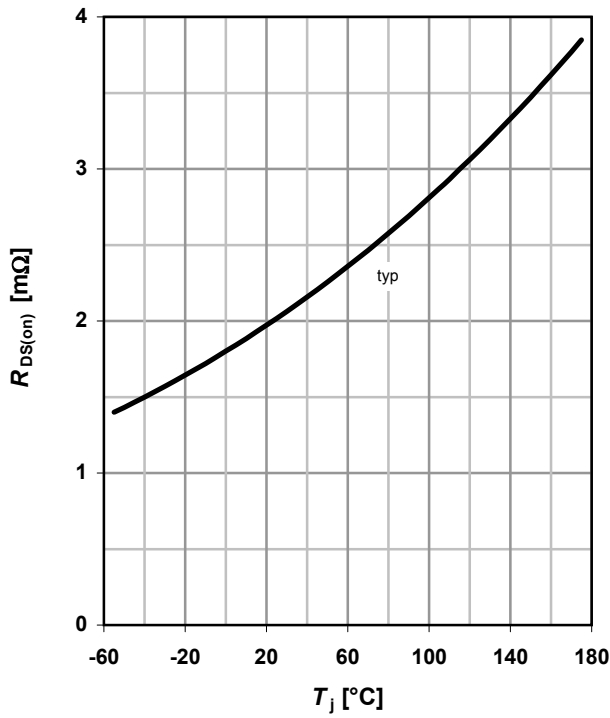
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

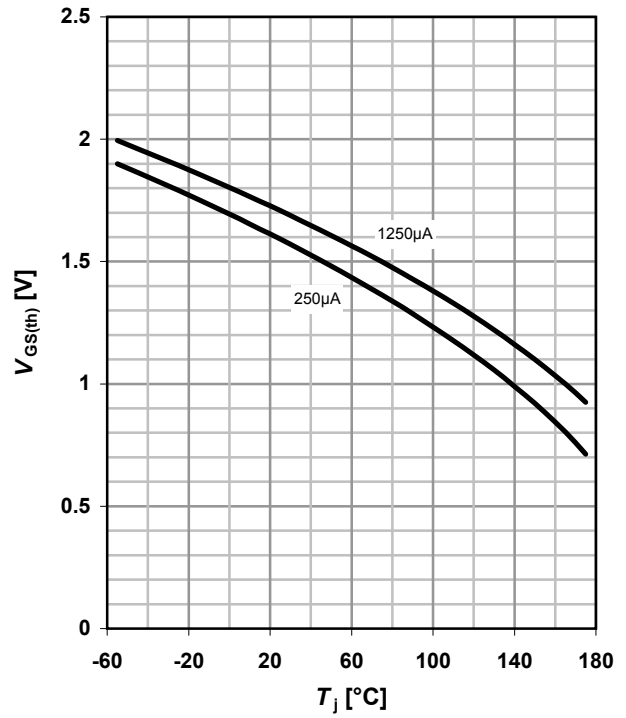
$R_{DS(on)}=f(T_j); I_D=60\text{ A}; V_{GS}=10\text{ V}$



**10 Typ. gate threshold voltage**

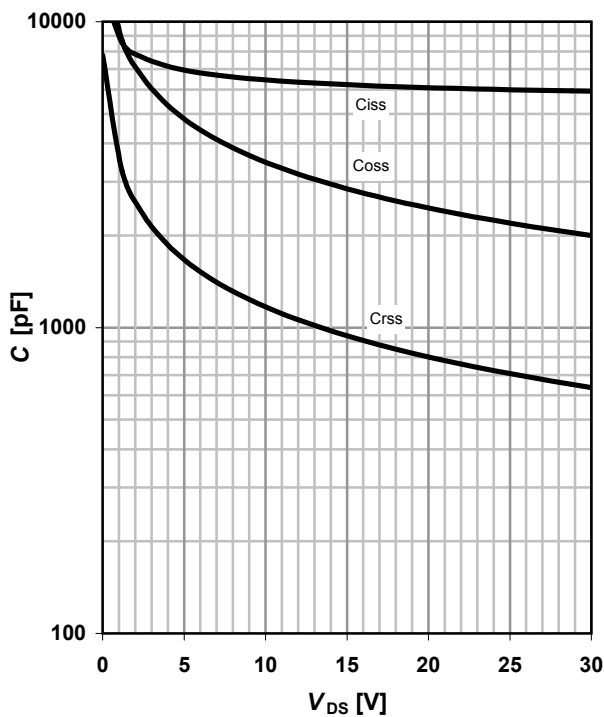
$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

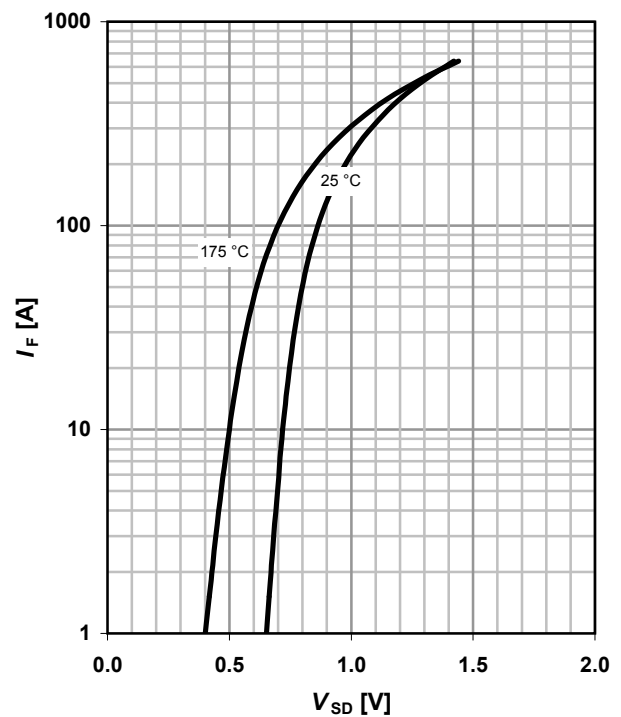
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



**12 Typ. Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

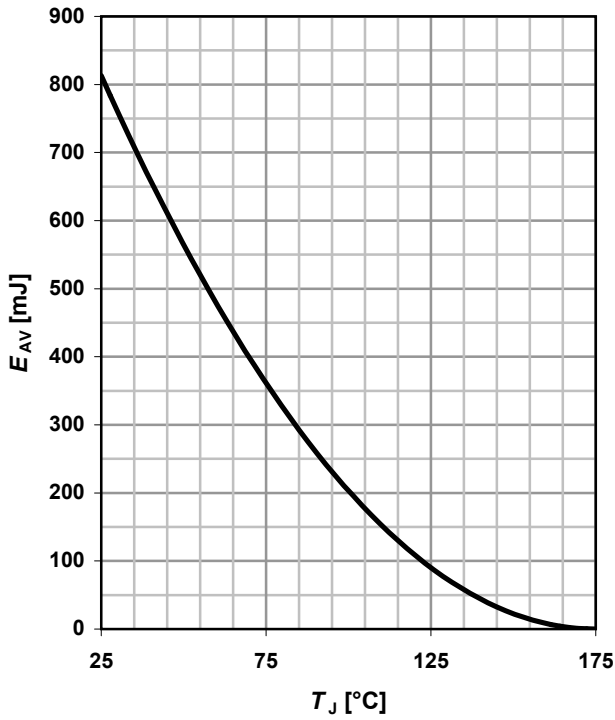
parameter:  $T_j$



**13 Typ. avalanche energy**

$E_{AS}=f(T_J)$

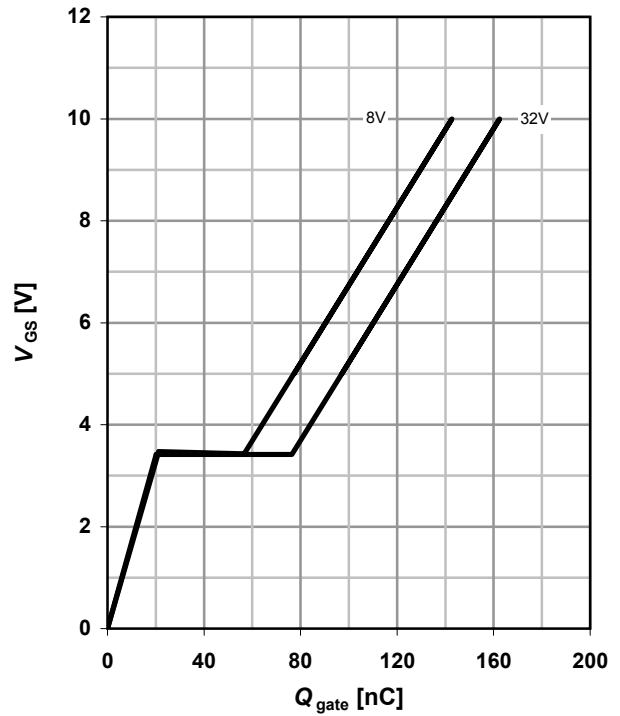
parameter:  $I_D=80A, V_{DD}=25V$



**14 Typ. gate charge**

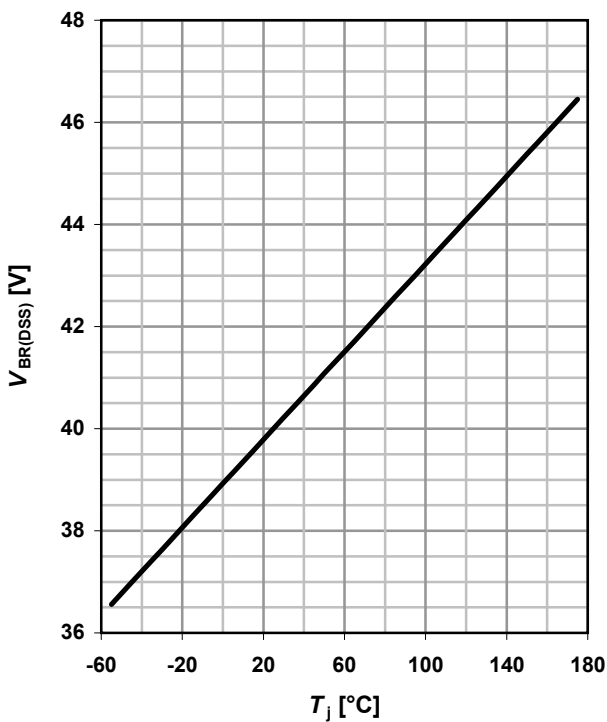
$V_{GS}=f(Q_{gate}); I_D=160A$  pulsed

parameter:  $V_{DD}$



**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 mA$



**16 Gate charge waveforms**



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